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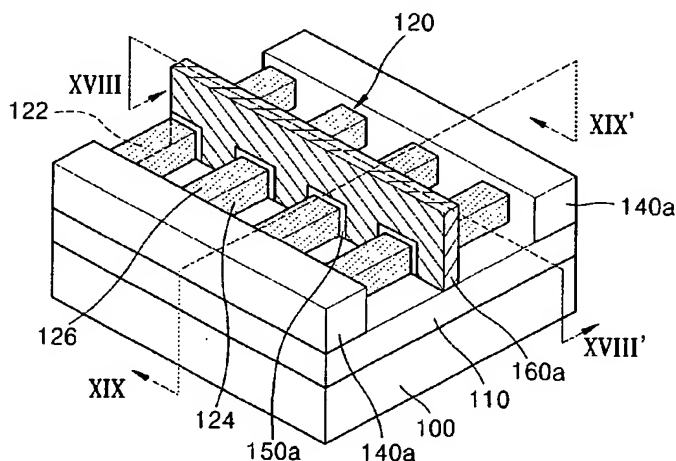
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(54) Title: SEMICONDUCTOR DEVICE HAVING MULTI-GATE STRUCTURE AND METHOD OF MANUFACTURING THE SAME



(57) Abstract: Provided are a semiconductor device having a mesa-type active region including a plurality of slabs and a method of manufacturing the semiconductor device. The semiconductor device includes a first active region and a second active region. The first active region is formed in a line-and-space pattern on a substrate and includes the slabs, each slab having a first surface, a second surface facing a direction opposite to the first side, and a top surface. The first active region and the second active region are composed of identical or different materials. The second active region contacts at least one end of each of the slabs on the substrate to connect the slabs to one another. The method includes forming a first active region in a line-and-space pattern on the substrate and forming the second active region.